

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	20	chang-ko-hsing.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:12
L3	11	huang-chiu-tsung.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:12
L4	2	"6821849".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:15
L5	2	"6794710".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:15
L6	2	"6768162".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:15
L7	2	"6737700".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:16
L8	2	"6635533".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:16
L9	2	"6117748".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:17

L10	2	"6103575".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:17
L11	2	"6096603".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:17
L12	2	"6026028".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:18
S1	1031	257/314.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:47
S2	969	257/321.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:47
S3	677	257/324.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:48
S4	159	257/325.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:48
S5	225	257/333.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:53

S6	711	257/411.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 16:55
S7	138	257/638.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 17:57
S8	19	composite adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:29
S9	9	composite adj gate adj insulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:00
S10	0	composite adj gate adj insulative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:00
S11	112	composite adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:13
S12	62	ono adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:28
S13	9	ono adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:10

S14	7	ono adj gate adj insulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:11
S15	0	ono adj gate adj insulative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:11
S16	9	ono adj gate adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:11
S17	30	composite adj gate adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:24
S18	0	(silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide) adj gate adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:26
S19	0	(silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide) adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:25
S20	0	(silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide) adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:25
S21	0	(silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide) adj gate adj insulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:25

S22	0	(silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide) adj gate adj insulative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:25
S23	0	(silicon adj oxide) adj (silicon adj nitride) adj (silicon adj oxide) adj gox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:25
S24	0	(sio) adj (sin) adj (sio) adj gate adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:27
S25	0	(sio) adj (sin) adj (sio) adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:27
S26	0	(sio) adj (sin) adj (sio) adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:28
S27	0	(sio) adj (sin) adj (sio) adj gate adj insulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:27
S28	0	(sio) adj (sin) adj (sio) adj gate adj insulative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:27
S29	0	(sio) adj (sin) adj (sio) adj gox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:27

S30	0	(sio) adj (sin) adj gox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:27
S31	0	(sio) adj (sin) adj gate adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:27
S32	0	(sio) adj (sin) adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:27
S33	0	(sio) adj (sin) adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:28
S34	0	(sio) adj (sin) adj gate adj insulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:28
S35	0	(sio) adj (sin) adj gate adj insulative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:28
S36	2	ono adj gox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:28
S37	0	composite adj gox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:35

S38	15	compound adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:36
S39	5	compound adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:37
S40	2	compound adj gate adj insulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:38
S41	0	compound adj gate adj insulative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:38
S42	1	compound adj gox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:38
S43	0	alternating adj gox	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:39
S44	0	alternating adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:40
S45	0	alternating adj gate adj oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:40

S46	0	alternating adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:40
S47	0	alternating adj gate adj insulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:40
S48	0	alternating adj gate adj insulative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:40
S49	0	ono adj between adj gate adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:41
S50	1	ono near gate near substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:41
S51	933	ono with gate with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:42
S52	63	stacked adj gate adj dielectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:47
S53	21	stacked adj gate adj insulator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:48

S54	36	stacked adj gate adj insulation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:51
S55	3	stacked adj gate adj insulative	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:53
S57	36	(dielectric adj stack) near ono	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:57
S58	1	(insulator adj stack) near ono	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:57
S59	0	(insulation adj stack) near ono	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:58
S60	0	(insulative adj stack) near ono	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 18:58
S61	290	(ono adj stack)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 19:10
S62	5	sonos adj rom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 19:11

S64	513	sonos and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 20:38
S65	370	sonos and "257"/\$.ccls. and thickness	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:25
S66	0	hyun-khe-yoo.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:26
S68	0	khe-yoo.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:26
S69	2	hyun-yoo.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:27
S70	0	ko-hsing-chang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:27
S71	1	ko-chang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:27
S72	4	hsing-chang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:28

S73	0	chiu-tsung-huang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:28
S74	1	chiu-huang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:28
S75	0	tsung-huang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:50
S76	2	"6137718".pn. and charge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:53
S77	1	"6137718".pn. and tunneling	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:54
S78	1	"6137718".pn. and tunnel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/03 21:54
S79	20	chang-ko-hsing.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 01:11
S80	0	chiu-tsung-huang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 12:42

S81	0	chiu-tsung-huang.inv.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/06 12:42
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